BUX66

NPN Silicon Low Frequency High Power Switching Transistor

Features:

1. Heavy working current.Good temperature stability.Excellent thermal fatigue capability.
2. Good Switching Characteristic.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	Test Condition
Total Dissipation	P_{tot}	W	35	Tc=25°C
Max. Collector Current	I_{CM}	A	2	
Junction Temperature	T_{jm}	°C	175	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	V	200	I_C=1mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	150	I_C=1mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	V	6	I_E=1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	2.5	I_C=1A,I_B=0.15A
Collector-Base Laekage Current	I_{CBO}	uA	10	V_{CB}=200V
Collector-Emitter Laekage Current	I_{CEO}	uA	100	V_{CE}=100V
Emitter-Base Leakage Current	I_{EBO}	mA	1	V_{EB}=6V
DC Current Gain	h_{FE}		10~60	V_{CE}= 5V, I_C=1A
Delay Time	t_d	us	-	V_{CE}= 20V, I_C=1A, I_{B1}=0.1A,I_{B2}=-0.1A
Rise Time	t_r	us	0.6	
Storage Time	t_s	us	2.5	
Fall Time	t_f	us	0.6	

Outline and Dimensions: